IXYS UK WESTCODE

Date:- 28th August, 2012

Data Sheet Issue:- A2

Provisional Data

Phase Control Thyristor

Types N3790T#240 to N3790T#280

Development Type No.: NX223TJ280

Absolute Maximum Ratings

	VOLTAGE RATINGS	MAXIMUM LIMITS	UNITS
V_{DRM}	Repetitive peak off-state voltage, (note 1)	2400-2800	V
V_{DSM}	Non-repetitive peak off-state voltage, (note 1)	2400-2800	V
V_{RRM}	Repetitive peak reverse voltage, (note 1)	2400-2800	V
V_{RSM}	Non-repetitive peak reverse voltage, (note 1)	2500-2900	V

	OTHER RATINGS		MAXIMUM LIMITS	UNITS
$I_{T(AV)M}$	Maximum average on-state current, T_{sink}=55°C, (note 2)		3790	A
$I_{T(AV)M}$	Maximum average on-state current. T_{sink}=85°C, (note 2)		2655	A
$I_{T(AV)M}$	Maximum average on-state current. T_{sink}=85°C, (note 3)		1405	A
$I_{T(RMS)M}$	Nominal RMS on-state current, T_{sink}=25°C, (note 2)		7410	A
$I_{T(d.c.)}$	D.C. on-state current, T_{sink}=25°C, (note 4)		6610	A
I_{TSM}	Peak non-repetitive surge t_p=10ms, V_{rm}=60%V_{RRM}, (note 5)		49.5	kA
I_{TSM2}	Peak non-repetitive surge t_p=10ms, V_{rm}≤10V, (note 5)		55.0	kA
I^2t	I^2t capacity for fusing t_p=10ms, V_{rm}=60%V_{RRM}, (note 5)		12.3×10^6	A^2s
I^2t	I^2t capacity for fusing t_p=10ms, V_{rm}≤10V, (note 5)		15.1×10^6	A^2s
$(di/dt)_{cr}$	Critical rate of rise of on-state current (note 6)	(continuous, 50Hz)	100	A/µs
		(repetitive, 50Hz, 60s)	200	
		(non-repetitive)	400	
V_{RGM}	Peak reverse gate voltage		5	V
$P_{G(AV)}$	Mean forward gate power		5	W
P_{GM}	Peak forward gate power		40	W
$T_{j\ op}$	Operating temperature range		-40 to +125	°C
T_{stg}	Storage temperature range		-40 to +150	°C

Notes:-

1) De-rating factor of 0.13% per °C is applicable for T_j below 25°C.
2) Double side cooled, single phase; 50Hz, 180° half-sinewave.
3) Cathode side cooled, single phase; 50Hz, 180° half-sinewave.
4) Double side cooled.
5) Half-sinewave, 125°C T_j initial.
6) V_D=67% V_{DRM}, I_{TM}=2000A, I_{FG}=2A, t_r≤0.5µs, T_{case}=125°C.

Characteristics

	PARAMETER	MIN.	TYP.	MAX.	TEST CONDITIONS (Note 1)	UNITS
V_{TM}	Maximum peak on-state voltage	-	-	1.50	I_{TM}=4000A	V
V_{TM}	Maximum peak on-state voltage	-	-	2.10	I_{TM}=8000A	V
V_{T0}	Threshold voltage	-	-	0.90		V
r_T	Slope resistance	-	-	0.15		mΩ
$(dv/dt)_{cr}$	Critical rate of rise of off-state voltage	1000	-	-	V_D=80% V_{DRM}, linear ramp, gate o/c	V/µs
I_{DRM}	Peak off-state current	-	-	250	Rated V_{DRM}	mA
I_{RRM}	Peak reverse current	-	-	250	Rated V_{RRM}	mA
V_{GT}	Gate trigger voltage	-	-	3.0	T_j=25°C V_D=10V, I_T=3A	V
I_{GT}	Gate trigger current	-	-	300		mA
V_{GD}	Gate non-trigger voltage	-	-	0.25	Rated V_{DRM}	V
I_H	Holding current	-	-	1000	T_j=25°C	mA
t_{gd}	Gate-controlled turn-on delay time	-	0.7	1.5	V_D=67% V_{DRM}, I_T=2000A, di/dt=10A/µs, I_{FG}=2A, t_r=0.5µs, T_j=25°C	µs
t_{gt}	Turn-on time	-	2.0	4.0		µs
Q_{rr}	Recovered charge	-	7000	7700	I_{TM}=4000A, t_p=2000µs, di/dt=10A/µs, V_r=100V	µC
Q_{ra}	Recovered charge, 50% Chord	-	4500	-		µC
I_{rr}	Reverse recovery current	-	210	-		A
t_{rr}	Reverse recovery time	-	43	-		µs
t_q	Turn-off time	-	250	-	I_{TM}=4000A, t_p=2000µs, di/dt=10A/µs, V_r=100V, V_{dr}=80%V_{DRM}, dV_{dr}/dt=20V/µs	µs
		-	400	-	I_{TM}=4000A, t_p=2000µs, di/dt=10A/µs, V_r=100V, V_{dr}=80%V_{DRM}, dV_{dr}/dt=200V/µs	
R_{thJK}	Thermal resistance, junction to heatsink	-	-	0.008	Double side cooled	K/W
		-	-	0.013	Anode side cooled	K/W
		-	-	0.020	Cathode side cooled	K/W
F	Mounting force	60	-	70	Note 2.	kN
W_t	Weight	-	1.15	-		kg

Notes:-
1) Unless otherwise indicated T_j=125°C.
2) For other clamp forces, please consult factory.

Curves

Figure 1 – On-state characteristics of Limit device

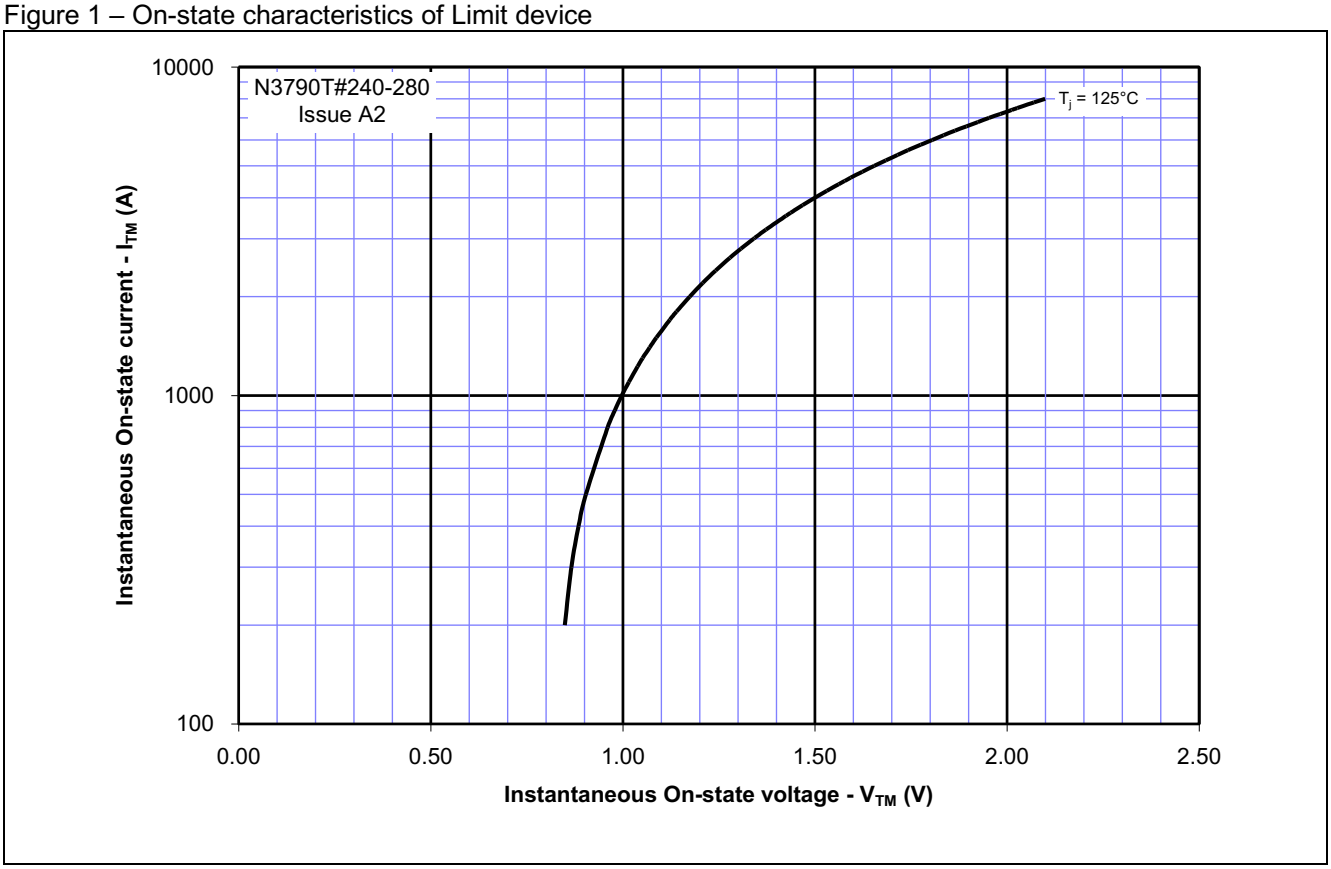


Figure 2 – Transient thermal impedance

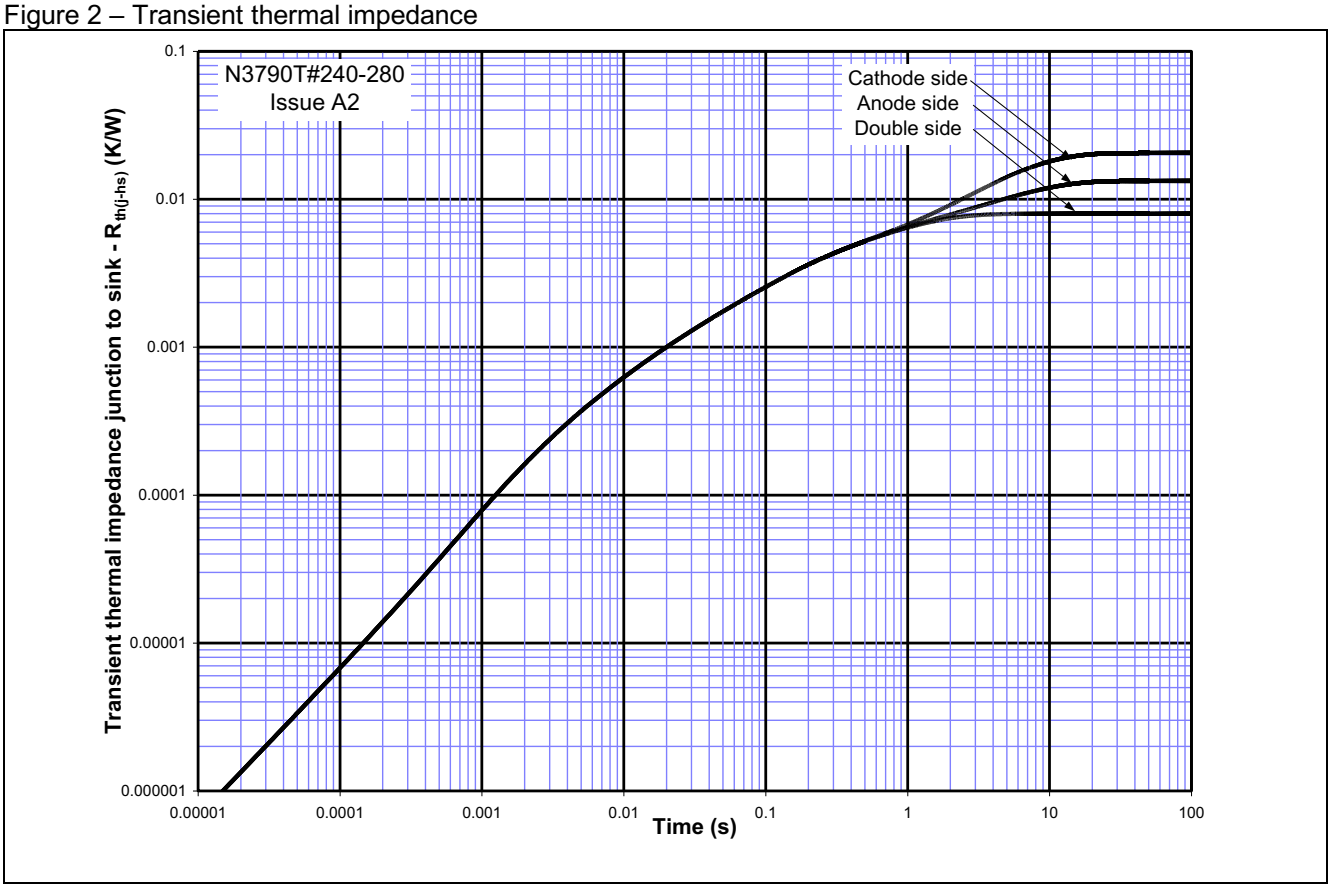
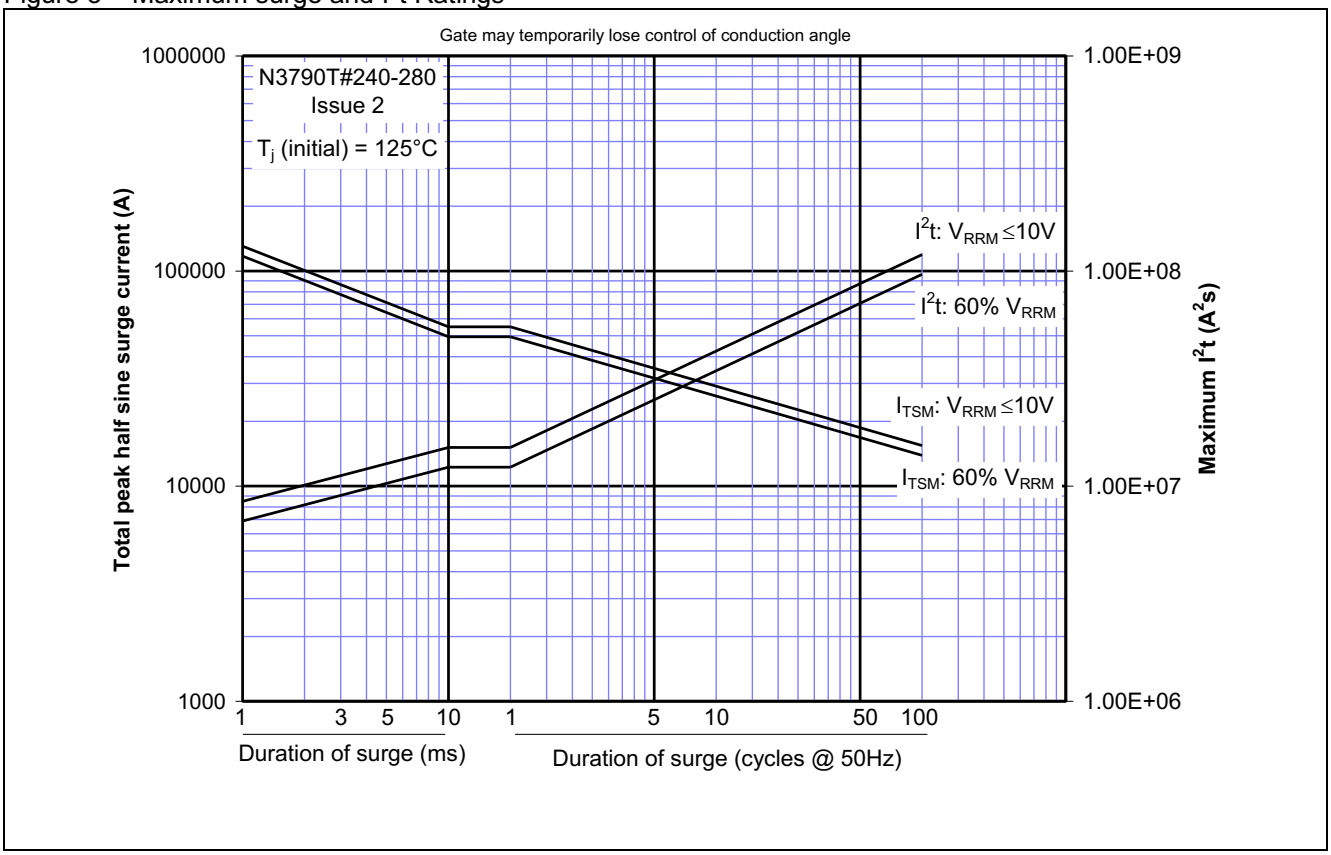
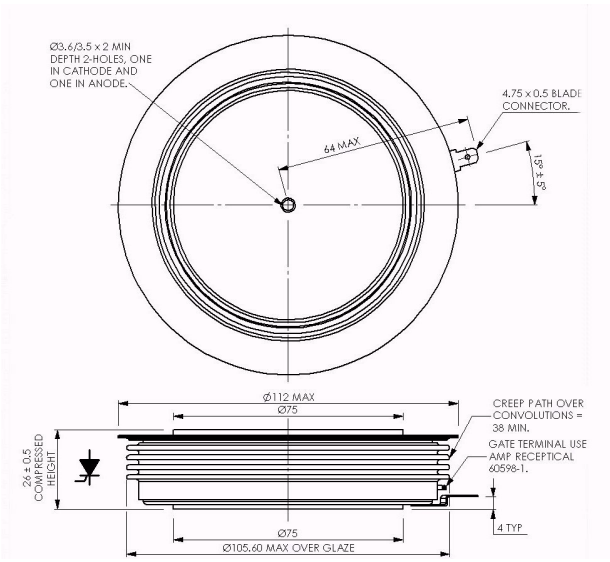


Figure 3 – Maximum surge and I^2t Ratings

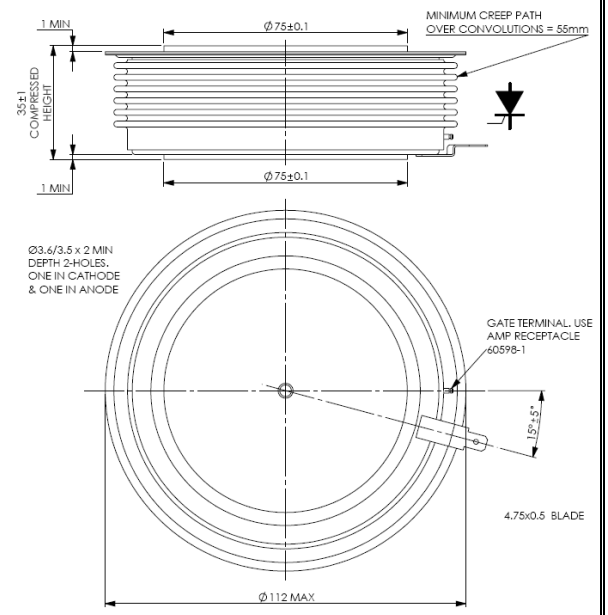


Outline Drawing & Ordering Information



101A373

Outline option TJ



101A395

Outline option TE

ORDERING INFORMATION		(Please quote 10 digit code as below)	
N3790	**T#**	**♦♦**	**0**
Fixed Type Code	Fixed TJ = 26mm clamp height TE = 35mm clamp height	Voltage code V_{DRM}/100 24-28	Fixed turn-off time code

Order code: N3790TJ280 – 2800V V_{DRM}, V_{RRM}, 26mm clamp height capsule.

IXYS Semiconductor GmbH
Edisonstraße 15
D-68623 Lampertheim
Tel: +49 6206 503-0
Fax: +49 6206 503-627
E-mail: marcom@ixys.de

IXYS UK Westcode Ltd
Langley Park Way, Langley Park,
Chippenham, Wiltshire, SN15 1GE.
Tel: +44 (0)1249 444524
Fax: +44 (0)1249 659448
E-mail: sales@ixysuk.com

IXYS Corporation
1590 Buckeye Drive
Milpitas CA 95035-7418
Tel: +1 (408) 457 9000
Fax: +1 (408) 496 0670
E-mail: sales@ixys.net

IXYS Long Beach
IXYS Long Beach, Inc
2500 Mira Mar Ave, Long Beach
CA 90815
Tel: +1 (562) 296 6584
Fax: +1 (562) 296 6585
E-mail: service@ixyslongbeach.com

www.ixysuk.com

www.ixys.com

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